

**Session Program**

**10-14 Nov 2025**

**4th DRD3 week on Solid State Detectors R&D**

***WG3/WP3 - Extreme fluence and radiation  
damage characterization***

CERN, 6/2-024 - BE Auditorium Meyrin

# Wednesday 12 November

10:50

## WG3/WP3 - Extreme fluence and radiation damage characterization: Scientific results & Project Proposals

Session | Location: CERN, 6/2-024 - BE Auditorium Meyrin

10:55-11:25 **Coffee break**

11:25-11:55 **Gain-Layer Project**

**Speaker**  
Niels Sorgenfrei

11:55-12:15

**Study of Irradiation-Induced Defects in EPI silicon PINs and LGADs by c/iDLTS**

**Speaker**  
Dr Yunyun Fan

12:15-12:35

**Optical detected magnetic resonance (ODMR) of  $A_{Si}-Si_i$ -defects: case of acceptor indium**

**Speaker**  
Kevin Lauer

12:35-12:55

**Study of radiation damages at extreme fluences by Infrared Spectroscopy**

**Speaker**  
Dr Faiza Rizwan

13:00

14:20

## WG3/WP3 - Extreme fluence and radiation damage characterization: Scientific results & Project Proposals

Session | Location: CERN, 6/2-024 - BE Auditorium Meyrin

14:20-14:40

**Investigation of point defects in silicon supercells using density functional theory**

**Speaker**  
George Alexandru Nemnes

14:40-15:00 **Donor removal and Global Gain Quenching (GGQ) in nLGAD detectors**

**Speaker**  
Milos Manojlovic

15:00-15:20

**Radiation hardness and annealing studies of double irradiated silicon diodes produced on 8-inch wafers for CMS HGICAL**

**Speaker**  
Max Andersson

15:20-15:50 **Coffee break**

15:50-16:10 **Studies of surface radiation damage with CMS HGAL test diodes**

**Speaker**

Eva Fialova

16:10-16:30

**Leakage current evolution in LHCb VELO sensors during Run 1-2 LHC data taking period.**

**Speaker**

Agnieszka Oblakowska-Mucha

16:30-16:50

**Annealing effects on highly n-doped layers in Resistive AC-coupled Silicon Detectors (RSD/AC-LGAD)**

**Speakers**

Aurora Losana, Brendan Regnery

16:50-17:10

**Response of AC-coupled Low Gain Avalanche Detectors to Ionizing and Non-ionizing Radiation Damage**

**Speaker**

Jiahe Si

17:10-17:30

**Defect investigation on n-type Schottky diodes based on 4H-SiC before and after irradiation with 6 MeV electrons**

**Speaker**

Andra-Georgia Boni

17:30-18:00

**WG3 - Updates and Discussion**

**Speakers**

Ioana Pintilie, Dr Joern Schwandt

18:00